

A DLTS study of 4H-SiC-based p-n junctions fabricated by boron implantation

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Impurity interaction with point defects in the Si-SiO₂ structures and its influence on the interface properties

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Investigation of strain relaxation mechanism in Si-SiO₂ system during the process of its formation

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Simulations of wide bandgap SiC N-N heterostructure diode

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Strain relaxation mechanism in the Si-SiO₂ system and its influence on the interface properties

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Structure-reactivity relationships for organosilicon compounds revisited

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Зависимость между содержанием P₂O₅ и SiO₂ в оболочках фосфоритов

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Создание и свойства высокоомных эпитаксиальных слоев кремния большой площади

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